

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional) BREV 12370	Application Number 09/777,516
Applicant(s) ASPAR et al	# 10
Filing Date February 6, 2001	Group Art Unit 2823

*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
G	Ascheron, C., "A Comparative Study of Swelling, Radiation, Strain and Radiation Damage of High-Energy Proton-bombarded GaAs, GaP, InP, Si and Ge Single Crystals, Nuclear Instruments and Methods in Physics Research" Nuclear Instruments and Methods in Physics Research B36(1989) 163?172.
G	Ascheron, C., "A Study of Proton Bombardment Induced Swelling of GaP Single Crystals" phys. stat. sol. (a) 92, 169 (1985).
G	Ascheron, C., "Gettering of Copper in Proton-and Helium-Bombarded Buried Regions of Gallium Phosphide" phys. stat. sol. (a) 106, 73 (1988).
G	Ascheron, C., "Investigations of Hydrogen Implanted GaP Single Crystals by Means of Particle Induced ?-Spectroscopy, Infrared Spectroscopy, and Turyherford Backscattering Channeling Technique" phys. stat. sol. (a) 89, 549 (1985).
G	Ascheron, C., "Proton Beam Modification of Selected AlIIBV Compounds" phys. stat. sol. (a) 124, 11 (1991).
G	Ascheron, C., "Swelling, Strain, and Radiation Damage of He+ Implanted GaP" phys. stat. sol. (a) 96, 555 (1986).
G	Ascheron, C., "The Effect of Hydrogen Implantation Induced Stress on GaP Single Crystals" Nuclear Instruments and Methods in Physics Research B28 (1987) 350-359.
G	Bruel, M., "Silicon-On-Insulator" European Semiconductor, March 1997.
G	Cassidy, Victor M., "Ion Implantation Process Toughens Metalworking Tools," Modern Metals, pp. 65-67, 1984.
G	Chu et al, "Radiation Damage of 50-250 keV Hydrogen Ions in Silicon", Ion Implantation in Semiconductors, eds. F. Chernob et al., Plenum New York 1976, pp. 483-492.
G	Chu, P.K. et al., Plasma Immersion Ion Implantation-A Fledgling Technique for Semiconductor Processing, Materials Science and Engineering Reports: A Review Journal, pp. 207-280, vol. R17, Nos. 6-7, Nov. 30, 1996.
G	Chu, Kastle, Lever, Mader and Masters, S, Radiative Recombination Channels due to Hydrogen in Crystalline Silicon, Canham, Dyball Leong, Houlton, Cullis and Smith, Materials Science and Engineering, B4 (1989), pp. 41-45. Ion Implantation keV Hydrogen Ions in Silicon, , pp. 483-391.

EXAMINER

Fourgan

DATE CONSIDERED

5/10/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional) BREV 12370	Application Number 09/777,516
Applicant(s) ASPAR et al.	
Filing Date February 6, 2001	Group Art Unit 2823

*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>
G	Cullis, A.G., T.E. Seidel and R.L. Meek, "Comparative study of annealed neon-, argon-, and krypton-ion implantation damage in silicon," J. Appl. Phys., 49(10), pp. 5188-5198, Oct. 1978.
G	EerNisse, E., "Compaction of ion-implanted fused silica" Journal of Applied Physics, Vol. 45, No.1, January 1974.
G	EerNisse, E.P., "Role of Integrated Lateral Stress In Surface Deformation of He- implanted Surfaces" Journal of Applied Physics, Vol. 48, No. 1, January 1977.
G	Evans, J.H., "An Interbubble Fracture Mechanism Of Blister Formation On Helium-Irradiated Metals" Journal of Nuclear Materials 68(1977) 129-140.
G	menko, N., "Infrared Absorption of Silicon Irradiated by Protons" phys. stat.sol. (b) 90, 689 (1978).
G	Gerasimenko, N., "Infrared Absorption of Silicon Irradiated by Protons" phys. stat.sol. (b) 90, 689 (1978).
G	Greenwald, A.C., "Pulsed-electron-beam annealing of ion-implantation damage" J. Appl. Phys. 50(2), February 1978.
G	Grovenor, C.R.M., Microelectronic Materials, pp. 73-75 (1989).
G	Haisma et al., Silicon-on-Insulator Wafer Bonding-Wafer Thinning Technological Evaluations, Japanese Journal of Applied Physics, 28(1989), Aug., No. 8, Part 1, Tokyo, Japan, pp. 1426-1443.
G	Hamaguchi et al., Device Layer Transfer Technique using Chemi-Mechanical Polishing, Japanese Journal of Applied Physics, 23(1984), Oct., No. 10, Part 2, Tokyo, Japan, pp. L815-L817.
G	Helium Bubble and Blister Formation for Nickel and An Amorphous Fe-Ni-Mo-B Alloy During 5 keV He+-Irradiation at Temperatures Between 200 K and 600 K, Swijgenhoven, Stals and Knuyt, Nuclear Instruments and Methods 209/210 (1983) pp. 461-468.
G	Hulett, D.M. et al., "Ion Nitriding and Ion Implantation: A Comparison," Metal Progress, pp. 18-21, 1985.

EXAMINER

FOURSON

DATE CONSIDERED

5/10/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional) BREV 12370 JN3	Application Number 09/777,516
Applicant(s) ASPAR et al.	
Filing Date February 6, 2001	Group Art Unit 2823

*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
G	Japan Applied Physics; 64(8); October 15, 1988; pp. 3972-3974.
G	Johnson, P.B., "High Fluence Deuteron Bombardment of Silicon" Radiation Effect 1977, Vol. 32 pp. 159-167.
G	"Isolation by Inert Ion Implantation" IBM Technical Disclosure Bulletin Vol. 29, No. 3, August., 1986, p. 1416.
G	Klem, J.F., Characteristics of Lift-Off Fabricated AlGaAs/InGaAs Single-Strained-Quantum Well Structures On Glass and Silicon Substrates, Inst. Phys. Conf. Ser. No. 96: Chapter 6, pp. 387-392 (1989).
G	Li, J., "Novel Semiconductor Substrate Formed by Hydrogen Ion Implantation into Silicon," Appl. Phys. Lett., vol. 55, No. 21, pp. 2223-2224, Nov. 20, 1989.
G	Ligeon, E., "Hydrogen Implantation in Silicon Between 1.5 and 60 KeV" Radiation Effects 1976, Vol. 27, pp. 129-137
G	Manuaba, A., "Comparative Study on Fe32Ni36Cr14P12B 6 Metallic Glass and its Polycrystalline Modification bombarded by 2000 keV Helium Ions with High Fluence" Nuclear Instruments and Methods 199 (1982) 409-419.
G	Matsuda et al., "Large Diameter Ion Beam Implantation System," Nuclear Instruments and Methods, vol. B21, pp. 314-316, 1987.
G	Mishima, Y. and T. Yagishita, T. "Investigation of the bubble formation mechanism in a-Si:H films by Fourier-transform infrared mirospectroscopy" J. Appl. Phys., Vol. 64, No. 8, 15 October 1988.
G	Miyagawa, S., "Helium remission during implantation of silicon carbide" J. Appl. Phys. 54 (5), May 1983.
G	Miyagawa, S., "Surface structure of silicon carbide irradiated with helium ions with monoenergy and continuous energy distributions" J. Appl. Phys. 53(12), December 1982, pp.8697-8705.
G	Moreau, Wayne M., "Semiconductor Lithography, Principles, Practices, and Materials," Plenum Press, 1988. Table of Contents only.

EXAMINER

FOURSON

DATE CONSIDERED

5/10/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION
(Use several sheets if necessary)

Docket Number (Optional) BREV 12370 SN3	Application Number 09/777,516
Applicant(s) ASPAR et al.	
Filing Date February 6, 2001	Group Art Unit 2823

*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
G	Moriceau, H. et al, A New Characterization Process Used to Qualify SOI Films 1991 pp. 173-178.
G	Myers, D. R., "The effects of ion-implantation damage on the first-order Raman spectra of GaPa) J. Appl. Phys. 54(9), September 19??.
G	Neethling, J.H. et al., Identification of Hydrogen Platelets in Proton-Bombarded GaAs, 1985, pp. 941?-945.
G	Paszti, F., "Flaking and Wave-Like Structure on Metallic Glasses Induced by MeV-Energy Helium Ions" Nuclear Instruments and Methods 209/210(1983) 273-280.
G	Picraux, S. Thomas et al., "Ion Implantation of Surfaces," Scientific American, vol. 252, No. 3, pp. 102-113 1985.
G	Primak, W., "Impurity Effect in the Ionization Dilation of Vitreous Silica" J. Appl. Phys. 39(13) 1968.
G	Renier, M. et al., "A New Low-Engergy Ion Implanter for Bombardment of Cylindrical Surfaces," Vacuum, vol. 35, No. 12, pp. 577-578, 1985.
G	Roth, J., "Blistering and Bubble Formation" Inst. Phys. Conf. Ser. No. 28 © 1976: Chapter 7.
G	Sah, Chih-Tang et al., "Deactivation of the Boron Acceptor in Silicon by Hydrogen," Appl. Phys. Lett. 43(2), July 1983, pp. 204-06.
G	Sioshansi, Piran, "Ion Beam Modification of Materials for Industry," Thin Solid Film, vol. 118, pp. 61-71, 1984.
G	Snyman, H. C., "Transmission Electron Microscopy of Extended Crystal Defects in Proton Bombarded and Annealed GaAs" Radiation Effects, 1983, Vol. 69, pp. 199-230.
G	Snyman, H. C., "Void formation in annealed proton-bombarded GaAs."

EXAMINER

FOURSON

DATE CONSIDERED

5/10/04

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>		Docket Number (Optional) BREV 12370 N3	Application Number 09/777,516
		Applicant(s) ASPAR, et al.	
		Filing Date February 6, 2001	Group Art Unit 2823
*EXAMINER INITIAL	OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>		
G	Stephan, D., "Investigation of Lattice Strain in Proton-Irradiated GaP by a Modified Auleytner Technique" phys. stat. sol. (a) 87, pp. 589-96 (1985).		
G	Sze, S.M., VLSI Technology, 2.sup.nd Ed., pp. 9-10 (1988).		
G	Tzeng, J.C., "A Novel Self-Aligned Oxygen (Salox) Implanted SOI Mosfet Device Structure" Nuclear Instruments and Methods in Physics Research B2, pp. 112-15 (1987).		
G	U.S. Dept. of Energy, "The Fusion Connection: . . .", Plasma Coating, pp. 6-7, 1985.		
G	Veldkamp, W.B. et al., "Binary Optics," Scientific American, pp. 50-55, May 1992.		
G	Wemple, S.H., "Optical and channeling studies of ion-bombarded GaP" J. Appl. Phys., Vol. 45, No. 4, April 1974.		
G	Wolf, Stanley Ph.D., Silicon Processing for the VLSI Era (vol. 2), pp. 66-79, Lattice Press, 1990.		
EXAMINER <i>Fourson</i>		DATE CONSIDERED <i>5/10/04</i>	

***EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.